



#16  
RCE  
6-25-03  
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## REQUEST FOR CONTINUED EXAMINATION (RCE) TRANSMITTAL

Subsection (b) of 35 U.S.C. § 132, effective on May 29, 2000,  
provides for continued examination of an utility or plant  
application filed on or after June 8, 1995.  
See The American Inventors Protection Act of 1999 (AIPA).

|                        |                   |
|------------------------|-------------------|
| Application Number     | 09/736,140        |
| Filing Date            | December 15, 2000 |
| Examiner Name          | A. Williams       |
| First Named Inventor   | Toyokazu SAKATA   |
| Group Art Unit         | 2811              |
| Attorney Docket Number | 32011-168503      |

This is a Request for Continued Examination (RCE) under 37 C.F.R. § 1.114 of the above-identified application.  
**NOTE:** 37 C.F.R. § 1.114 is effective on May 29, 2000. If the above-identified application was filed prior to May 29, 2000, applicant may wish to consider filing a continued prosecution application (CPA) under 37 C.F.R. § 1.53 (d) (PTO/SB/29) instead of a RCE to be eligible for the patent term adjustment provisions of the AIPA. See Changes to Application Examination and Provisional Application Practice, Interim Rule, 65 Fed. Reg. 14865 (Mar. 20, 2000), 1233 Off. Gaz. Pat. Office 47 (Apr. 11, 2000), which established RCE practice.

1. Submission required under 37 C.F.R. § 1.114

- a. ☐ Previously submitted
- i. ☐ Consider the amendment(s)/reply under 37 C.F.R. § 1.116 previously filed on  
(Any unentered amendment(s) referred to above will be entered).
- ii. ☐ Consider the arguments in the Appeal Brief or Reply Brief previously filed on
- iii. ☐ Other
- b. Enclosed
- i. ☒ Amendment/Reply
- ii. ☐ Affidavit(s)/Declaration(s)
- iii. ☐ Information Disclosure Statement (IDS)
- iv. ☒ Other Substitute Specification and Formal Drawings

2. Miscellaneous

- a. ☐ Suspension of action on the above-identified application is requested under 37 C.F.R. § 1.103(c) for a period of \_\_\_\_\_ months. (Period of suspension shall not exceed 3 months; Fee under 37 C.F.R. § 1.17(i) required)
- b. ☐ Other

3. Fees The RCE fee under 37 C.F.R. § 1.17(e) is required by 37 C.F.R. § 1.114 when the RCE is filed.

- a. ☒ The Director is hereby authorized to charge the following fees, or credit any overpayments, to Deposit Account No. 22-0261
- i. ☐ RCE fee required under 37 C.F.R. § 1.17(e)
- ii. ☐ Extension of time fee (37 C.F.R. §§ 1.136 and 1.17)
- iii. ☐ Other
- b. ☒ Check in the amount of \$ 750.00 enclosed
- c. ☐ Payment by credit card (Form PTO-2038 enclosed)

### SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT REQUIRED

|                    |                  |                                   |         |
|--------------------|------------------|-----------------------------------|---------|
| Name (Print /Type) | James R. Burdett | Registration No. (Attorney/Agent) | 31,594  |
| Signature          |                  | Date                              | 6/16/03 |

VENABLE  
P.O. Box 34385  
Washington, DC 20043-9988

SEND Fees and Completed Forms to the following address: Commissioner for Patents, Box RCE, Washington, DC 20231.  
PC Docs No. 2/463567

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ATTORNEYS AT LAW

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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In re PATENT APPLICATION of

Applicants : Toyokazu SAKATA

Appln. No. : 09/736,140

Filed : December 15, 2000

For : SEMICONDUCTOR DEVICE WITH  
REDUCED INTERCONNECTION  
CAPACITY (as amended)

Examiner : A. Williams

Art Unit : 2811

Atty. Dkt. : 32011-168503

) Customer No.



26694

PATENT TRADEMARK OFFICE

AMENDMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

In response to the Office Action of March 18, 2003, please amend this application  
as follows:

IN THE CLAIMS:

Please amend the claims as follows:

1. (Twice Amended) A semiconductor device, comprising:
- an underlayer;
- a base oxide film with first holes and formed on the underlayer;
- a plurality of nitride film patterns, each having a hole pattern, respectively,
- formed on the base oxide film and directly connected to said first holes, respectively;

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